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Team Nexperia



Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- Very low Drain-Source on-state resistance R_{DSon} = 49 mΩ
- Very fast switching

3. Applications

- · Low-side load switch and charging switch for portable devices
- Power management in battery-driven portables
- LED driver
- DC-to-DC converters

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	3.2	А
Static chara	acteristics						_
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 3.2 A; T _j = 25 °C		-	49	55	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



30 V, N-channel Trench MOSFET

5. Pinning information

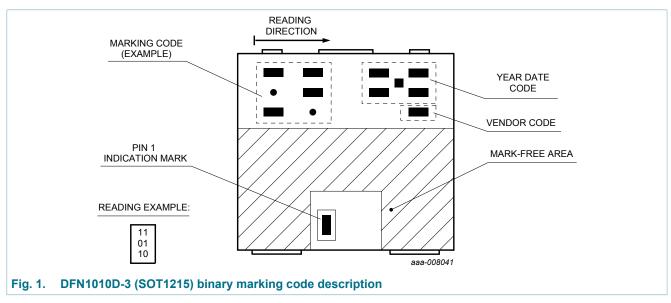
Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	G	gate		D				
2	S	source						
3	D	drain		G L F A				
4	D	drain	Transparent top view DFN1010D-3 (SOT1215)	S 017aaa253				

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMXB56EN	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215			

7. Marking

Table 4. Marking codes Type number Marking code PMXB56EN 01 10 10



30 V, N-channel Trench MOSFET

8. Limiting values

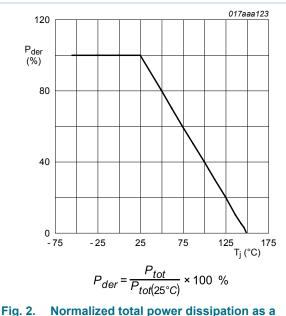
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

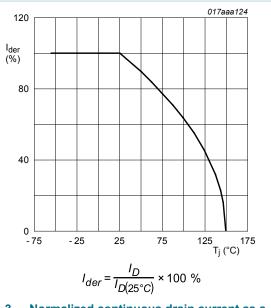
Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	3.2	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	2.8	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	15	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	0.4	W
			[1]	-	1.07	W
		T _{sp} = 25 °C		-	8.33	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
ls	source current	T _{amb} = 25 °C	[1]	-	1	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

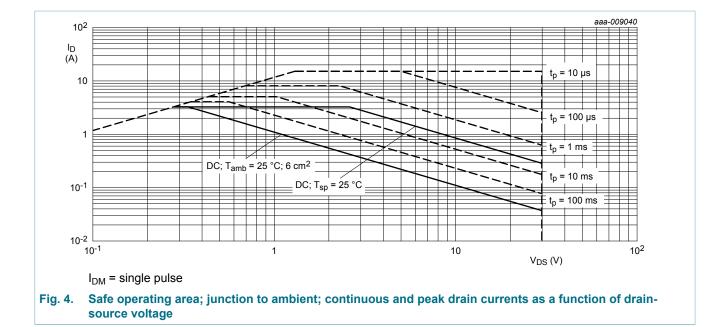


function of junction temperature





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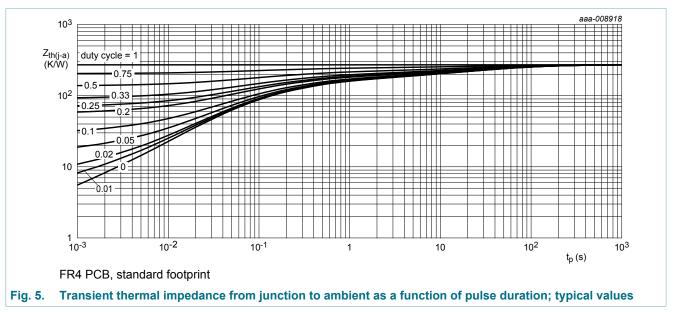


9. Thermal characteristics

Table 6. The	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	271	312	K/W
			[2]	-	102	117	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

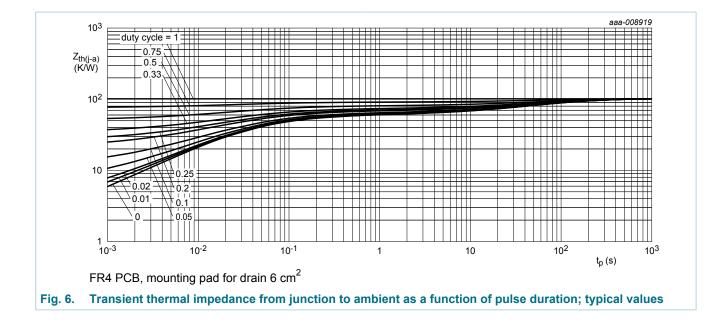
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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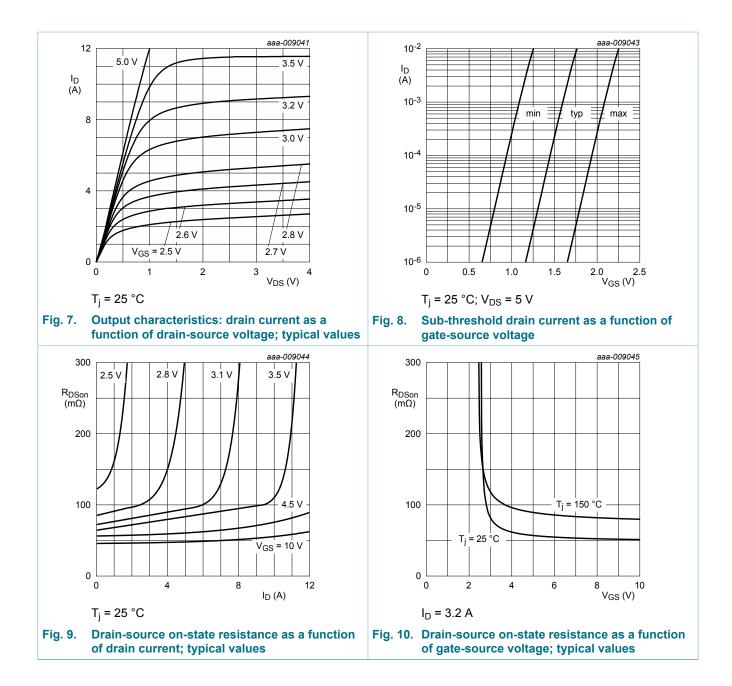
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$	1	1.5	2	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 3.2 A; T _j = 25 °C	-	49	55	mΩ
	resistance	V _{GS} = 10 V; I _D = 2.8 A; T _j = 150 °C	-	77	87	mΩ
		V_{GS} = 4.5 V; I _D = 3.2 A; T _j = 25 °C	-	56	65	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 3.2 A; T _j = 25 °C	-	13	-	S
R _G	gate resistance	T _j = 25 °C; f = 1 MHz	-	2.3	-	Ω
Dynamic ch	aracteristics	· · · ·	1	1		
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_D = 3.2 A; V_{GS} = 10 V;	-	3.6	6.3	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.5	-	nC
Q _{GD}	gate-drain charge		-	0.4	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	209	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	50	-	pF
C _{rss}	reverse transfer capacitance		-	17	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I_{D} = 3.2 A; V_{GS} = 10 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	12	-	ns
t _{d(off)}	turn-off delay time] [-	11	-	ns
t _f	fall time		-	2	-	ns
Source-drai	n diode		·			
V _{SD}	source-drain voltage	I _S = 1 A; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	V

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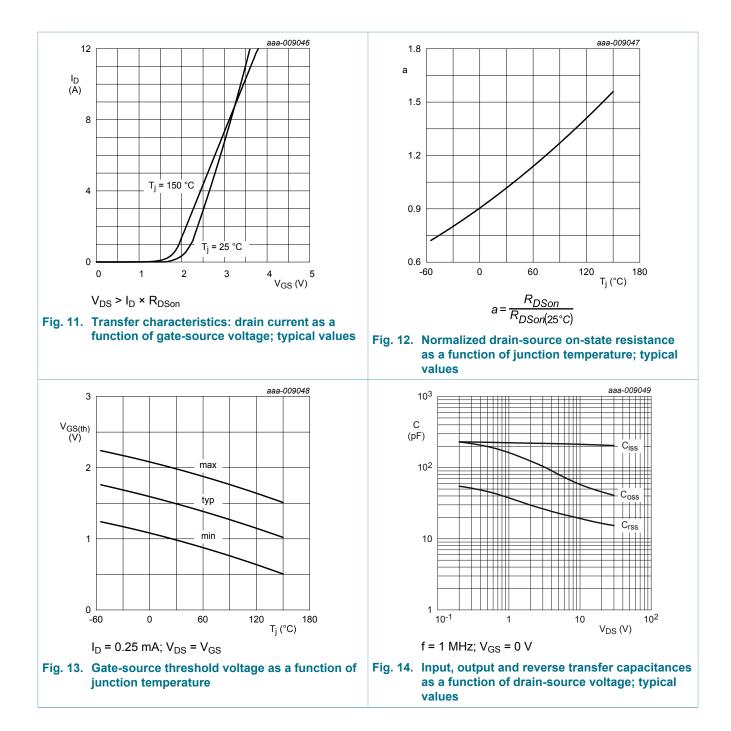
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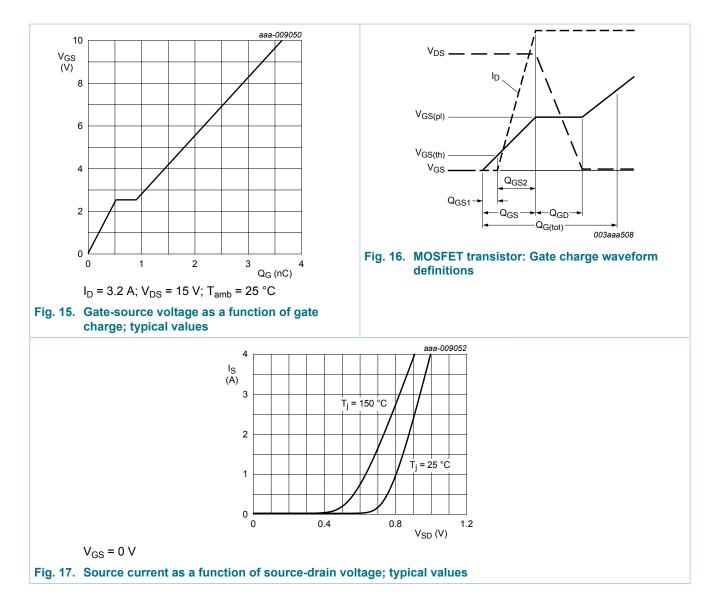


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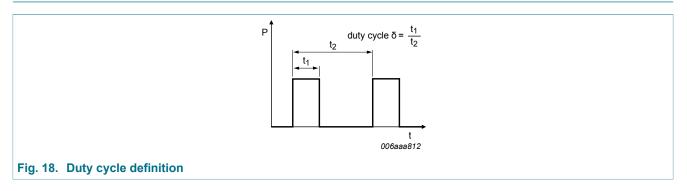
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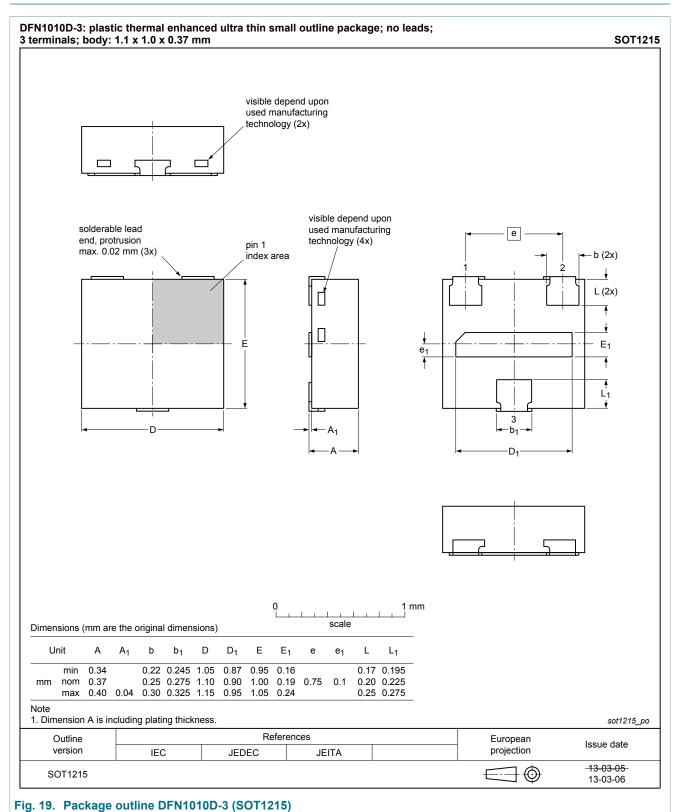


11. Test information



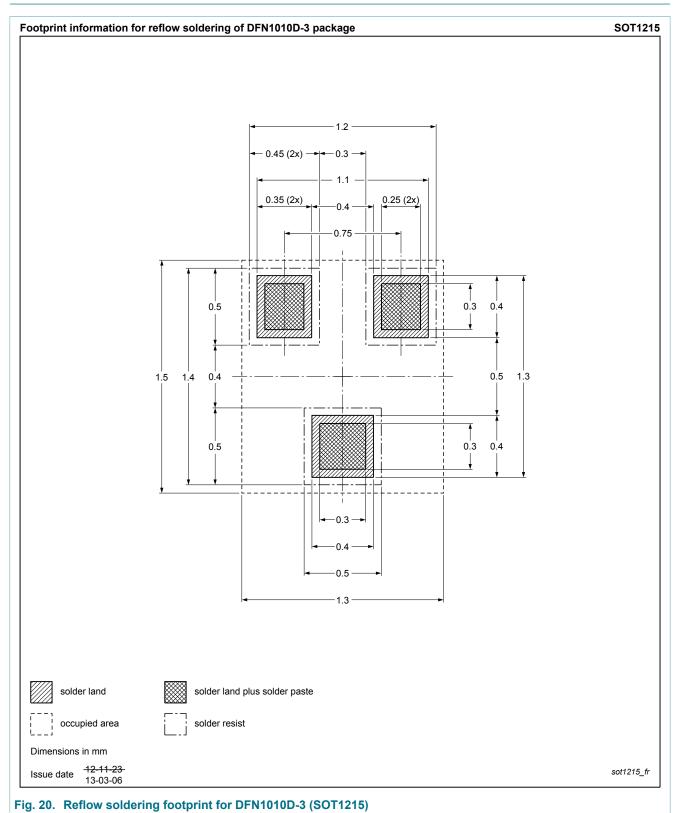
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMXB56EN v.3	20170111	Product data sheet	-	PMXB56EN v.2				
Modification:	Section 10. Cha	ard transconductance a	and gate resistance changed					
PMXB56EN v.2	20140430	Product data sheet	-	PMXB56EN v.1				
PMXB56EN v.1	20130925	Product data sheet	-	-				

30 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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